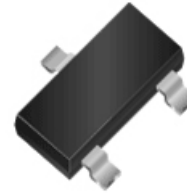


WNM2034

N-Channel, 20V, 3.6A, Power MOSFET

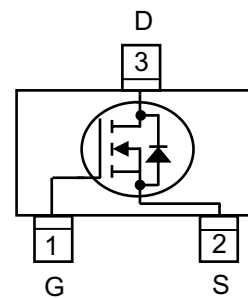
V _{DS} (V)	R _{dson} (Ω)
20	0.037 @ 10V
	0.045 @ 4.5V



SOT-23

Descriptions

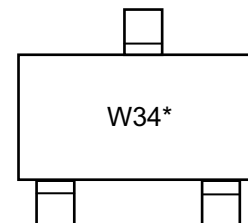
The WNM2034 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS (ON)} with low gate charge. This device is suitable for use in DC-DC conversion and power switch applications. Standard Product WNM2034 is Pb-free.



Configuration (Top View)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package SOT-23



W34 = Device Code
* = Month (A~Z)

Marking

Applications

- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch

Order Information

Device	Package	Shipping
WNM2034-3/TR	SOT-23	3000/Tape&Reel

WNM2034

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted					
Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current ($T_J = 150\text{ }^\circ\text{C}$) ^a	$T_A = 25\text{ }^\circ\text{C}$	I_D	3.6	3.3	A
	$T_A = 70\text{ }^\circ\text{C}$		2.8	2.6	
Maximum Power Dissipation ^a	$T_A = 25\text{ }^\circ\text{C}$	P_D	0.8	0.7	W
	$T_A = 70\text{ }^\circ\text{C}$		0.5	0.4	
Continuous Drain Current ($T_J = 150\text{ }^\circ\text{C}$) ^b	$T_A = 25\text{ }^\circ\text{C}$	I_D	3.2	3	A
	$T_A = 70\text{ }^\circ\text{C}$		2.6	2.4	
Maximum Power Dissipation ^b	$T_A = 25\text{ }^\circ\text{C}$	P_D	0.6	0.5	W
	$T_A = 70\text{ }^\circ\text{C}$		0.4	0.3	
Pulsed Drain Current ^c		I_{DM}	10		A
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	$t \leq 10\text{ s}$	$R_{\theta JA}$	125	150	$^\circ\text{C/W}$
	Steady State		140	175	
Junction-to-Ambient Thermal Resistance ^b	$t \leq 10\text{ s}$	$R_{\theta JA}$	150	180	
	Steady State		165	210	
Junction-to-Case Thermal Resistance		$R_{\theta JC}$	60	75	

- a Surface mounted on FR4 Board using 1 in sq pad size, 1oz Cu.
- b Surface mounted on FR4 board using the minimum recommended pad size, 1oz Cu.
- c Repetitive rating, pulse width limited by junction temperature, $t_p = 10\mu\text{s}$, Duty Cycle=1%
- d Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150\text{ }^\circ\text{C}$.

Electronics Characteristics

(Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1.0	1.5	2.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.6\text{ A}$		37	47	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 3.0\text{ A}$		45	56	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 3.6\text{ A}$		5.3		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz},$ $V_{DS} = 10\text{ V}$		505		pF
Output Capacitance	C_{OSS}			60		
Reverse Transfer Capacitance	C_{RSS}			50		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V},$ $I_D = 3.1\text{ A}$		11.4		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.90		
Gate-to-Source Charge	Q_{GS}			1.18		
Gate-to-Drain Charge	Q_{GD}			2.1		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_d(ON)$	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V},$ $R_L = 3\ \Omega, R_G = 6\ \Omega$		4.4		ns
Rise Time	t_r			3.2		
Turn-Off Delay Time	$t_d(OFF)$			24.5		
Fall Time	t_f			3.2		
SOURCE-to-DRAIN DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 1.5\text{ A}$	0.80	0.95	1.50	V